

FDS8333C

30V N & P-Channel PowerTrench[®] MOSFETs

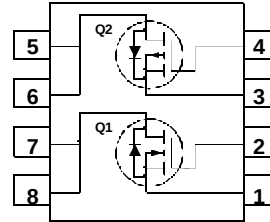
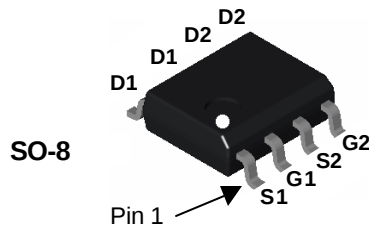
General Description

These N & P-Channel MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- **Q1** 4.1 A, 30V. $R_{DS(ON)} = 80\text{ m}\Omega @ V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 130\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- **Q2** -3.4 A, 30V. $R_{DS(ON)} = 130\text{ m}\Omega @ V_{GS} = -10\text{ V}$
 $R_{DS(ON)} = 200\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- Low gate charge
- High performance trench technology for extremely low $R_{DS(ON)}$.
- High power and handling capability in a widely used surface mount package.



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
V _{DSS}	Drain-Source Voltage	30	−30	V
V _{GSS}	Gate-Source Voltage	±16	±20	
I _b	Drain Current – Continuous (Note 1a)	4.1	−3.4	A
	– Pulsed	20	−20	
P _D	Power Dissipation for Dual Operation	2		W
	Power Dissipation for Single Operation (Note 1a)	1.6		
	(Note 1b)	1		
	(Note 1c)	0.9		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	−55 to +150		°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	40	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS8333C	FDS8333C	7"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

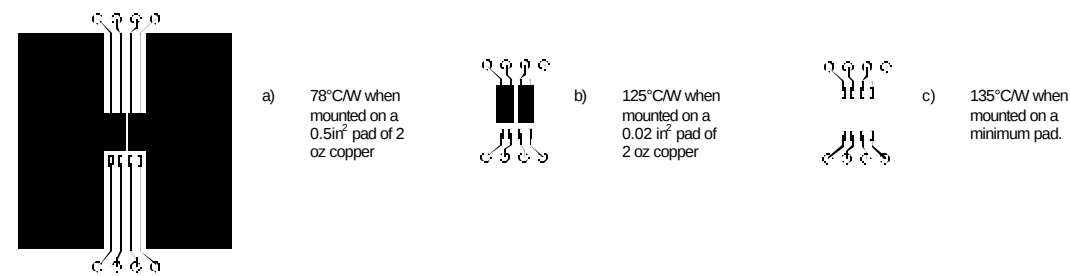
Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
Off Characteristics							
BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _b = 250 μA V _{GS} = 0 V, I _b = –250 μA		Q1 Q2	30 –30		V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _b = 250 μA, Ref. to 25°C I _b = –250 μA, Ref. to 25°C		Q1 Q2		25 –22	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = –24 V, V _{GS} = 0 V		Q1 Q2		1 –1	μA
I _{GSSF} / I _{GSSR}	Gate–Body Leakage, Forward	V _{GS} = ± 16 V, V _{DS} = 0 V				±100	nA
I _{GSSF} / I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = ± 20V , V _{DS} = 0 V				±100	nA
On Characteristics (Note 2)							
V _{GS(th)}	Gate Threshold Voltage	Q1	V _{DS} = V _{GS} , I _b = 250 μA	1	1.7	3	V
		Q2	V _{DS} = V _{GS} , I _b = –250 μA	–1	–1.8	–3	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _b = 250 μA, Ref. To 25°C I _b = –250 μA, Ref. to 25°C		Q1 Q2		–4.2 3.7	mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	Q1	V _{GS} = 10 V, I _b = 4.1 A V _{GS} = 4.5 V, I _b = 3.2 A V _{GS} = 10 V, I _b = 4.1 A T _J =125°C		67 81 103	80 130 145	mΩ
		Q2	V _{GS} = –10 V, I _b = –3.4 A V _{GS} = –4.5 V, I _b = –2.5 A V _{GS} = –10V, I _b = –3.4A, T _J =125°C		105 167 147	130 200 220	
I _{D(on)}	On–State Drain Current	Q1	V _{GS} = 10 V, V _{DS} = 5 V	10			A
		Q2	V _{GS} = –10 V, V _{DS} = –5 V	–5			
g _{FS}	Forward Transconductance	Q1	V _{DS} = 5 V I _b = 4.1 A		9		S
		Q2	V _{DS} = –5 V I _b = –3.4A		5		
Dynamic Characteristics							
C _{iss}	Input Capacitance	Q1	V _{DS} =10 V, V _{GS} = 0 V, f=1.0MHz		282		pF
		Q2	V _{DS} =–10 V, V _{GS} = 0 V, f=1.0MHz		185		
C _{oss}	Output Capacitance	Q1	V _{DS} =10 V, V _{GS} = 0 V, f=1.0MHz		49		pF
		Q2	V _{DS} =–10 V, V _{GS} = 0 V, f=1.0MHz		56		
C _{rss}	Reverse Transfer Capacitance	Q1	V _{DS} =10 V, V _{GS} = 0 V, f=1.0MHz		20		pF
		Q2	V _{DS} =–10 V, V _{GS} = 0 V, f=1.0MHz		26		
R _G	Gate Resistance	Q1	V _{GS} = 15 mV, f=1.0MHz		2.3		Ω
		Q2	V _{GS} =–15 mV, f=1.0MHz		–9.6		
Switching Characteristics (Note 2)							
t _{d(on)}	Turn–On Delay Time	Q1	For Q1: V _{DS} =10 V, I _{DS} = 1 A V _{GS} = 4.5 V, R _{GEN} = 6 Ω		4.5	9	ns
		Q2			4.5	9	
t _r	Turn–On Rise Time	Q1	For Q2: V _{DS} =–10 V, I _{DS} = –1 A V _{GS} = –4.5 V, R _{GEN} = 6 Ω		6	12	ns
		Q2			13	23	
t _{d(off)}	Turn–Off Delay Time	Q1			19	34	ns
		Q2			11	20	
t _f	Turn–Off Fall Time	Q1			1.5	3	ns
		Q2			2	4	
Q _g	Total Gate Charge	Q1	For Q1: V _{DS} =10 V, I _{DS} = 4.1 A V _{GS} = 4.5 V, R _{GEN} = 6 Ω		4.7	6.6	nC
		Q2			4.1	5.7	
Q _{gs}	Gate–Source Charge	Q1	For Q2: V _{DS} =–10 V, I _{DS} = –3.4 A V _{GS} = –4.5 V,		0.9		nC
		Q2			0.8		
Q _{gd}	Gate–Drain Charge	Q1			0.6		nC
		Q2			0.4		

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain–Source Diode Characteristics and Maximum Ratings						
V _{SD}	Drain–Source Diode Forward Voltage	Q1 V _{GS} = 0 V, I _S = 1.3 A (Note 2)		0.8	1.2	V
		Q2 V _{GS} = 0 V, I _S = –1.3 A (Note 2)		0.8	–1.2	
t _{rr}	Diode Reverse Recovery Time	Q1 I _F = 4.1 A, dI _F /dI = 100 A/μs		16.3		nS
		Q2 I _F = –3.4 A, dI _F /dI = 100 A/μs		14.5		
Q _{rr}	Diode Reverse Recovery Charge	Q1 I _F = 4.1 A, dI _F /dI = 100 A/μs		26.7		nC
		Q2 I _F = –3.4 A, dI _F /dI = 100 A/μs		21.1		

Notes:
1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

Typical Characteristics: N-Channel

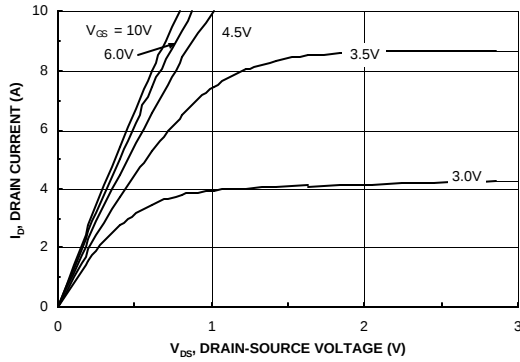


Figure 1. On-Region Characteristics.

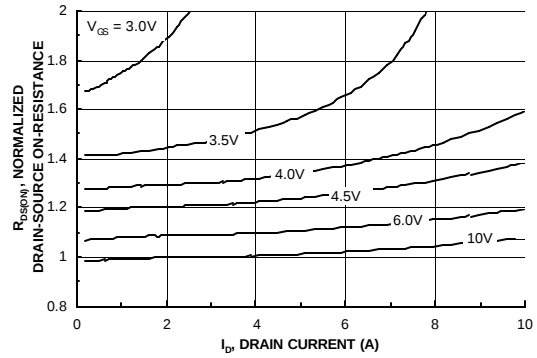


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

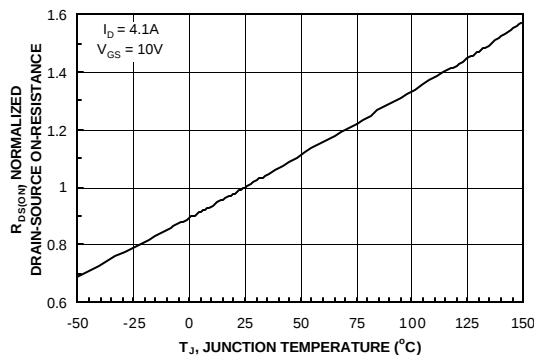


Figure 3. On-Resistance Variation with Temperature.

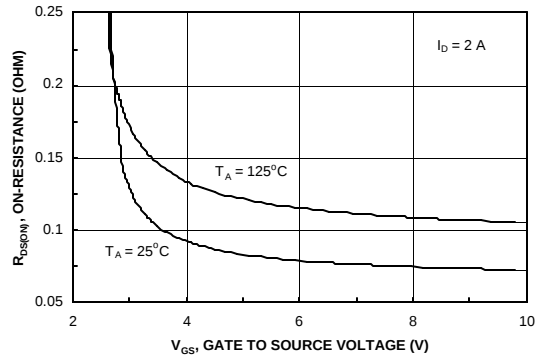


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

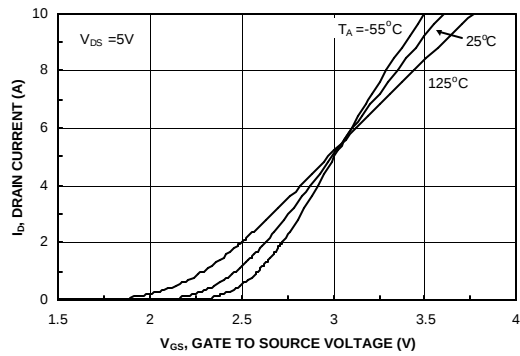


Figure 5. Transfer Characteristics.

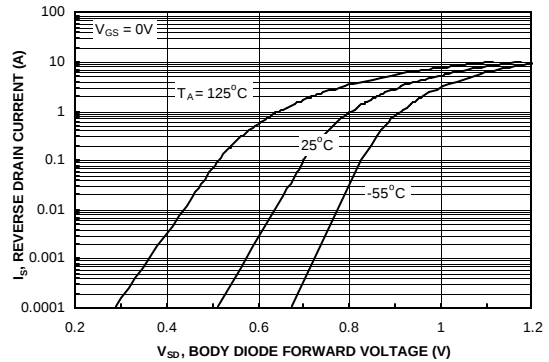


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics: N-Channel (continued)

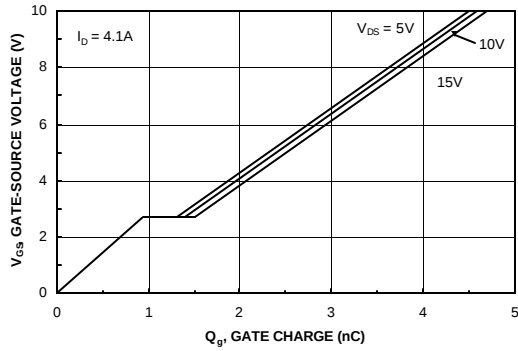


Figure 7. Gate Charge Characteristics.

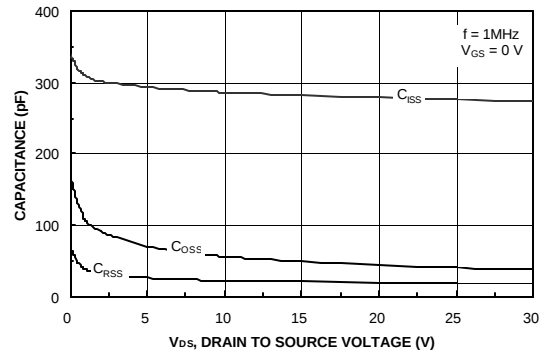


Figure 8. Capacitance Characteristics.

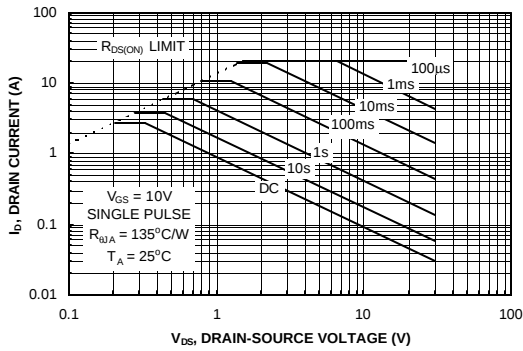


Figure 9. Maximum Safe Operating Area.

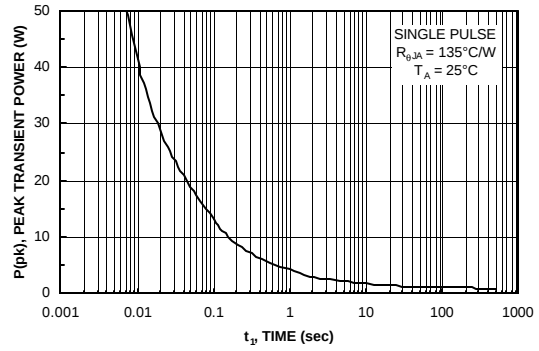


Figure 10. Single Pulse Maximum Power Dissipation.

Typical Characteristics: P-Channel

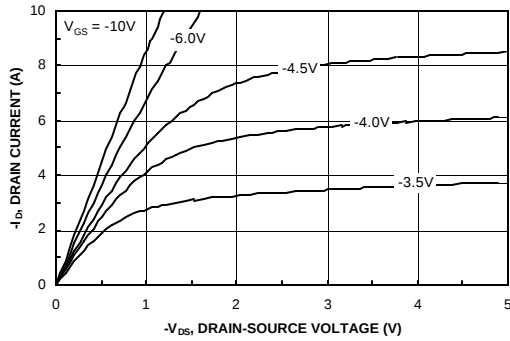


Figure 11. On-Region Characteristics.

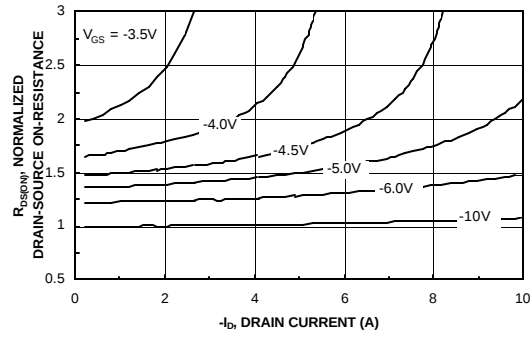


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

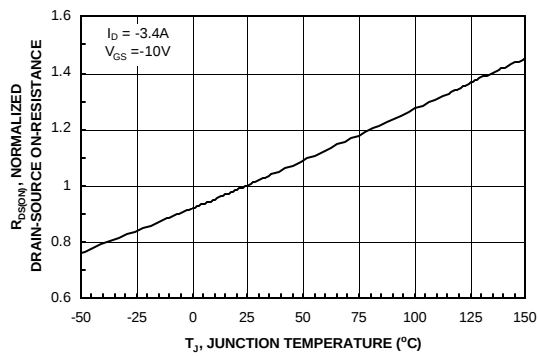


Figure 13. On-Resistance Variation with Temperature.

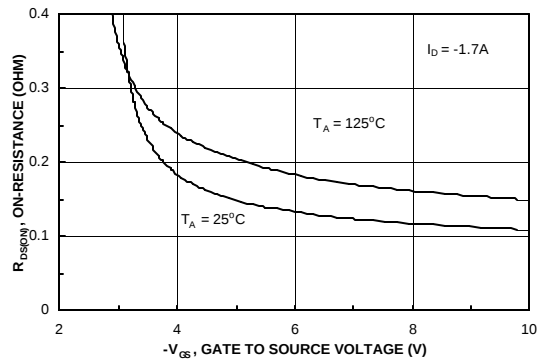


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

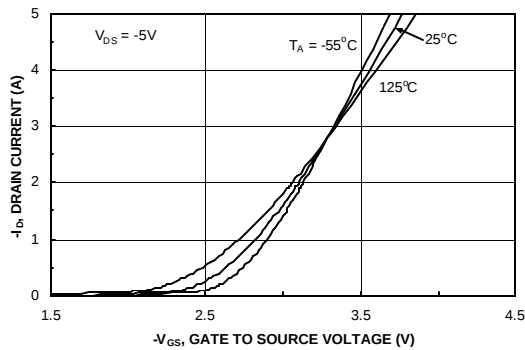


Figure 15. Transfer Characteristics.

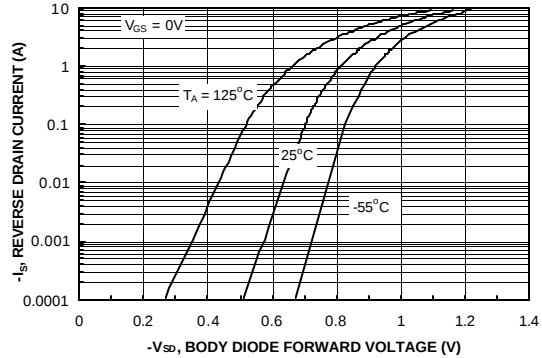


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics: P-Channel (continued)

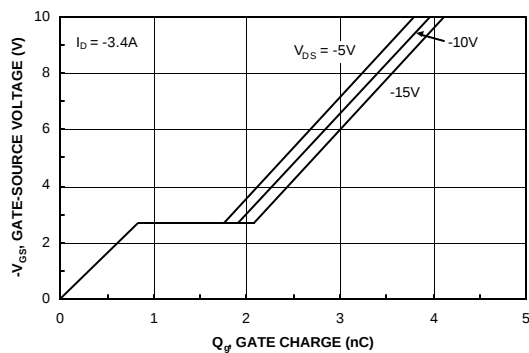


Figure 17. Gate Charge Characteristics.

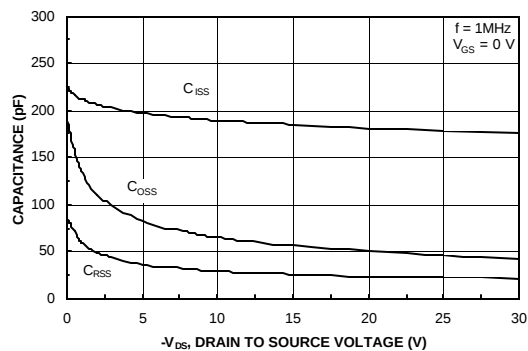


Figure 18. Capacitance Characteristics.

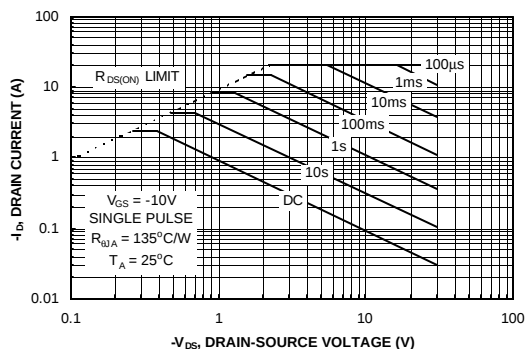


Figure 19. Maximum Safe Operating Area.

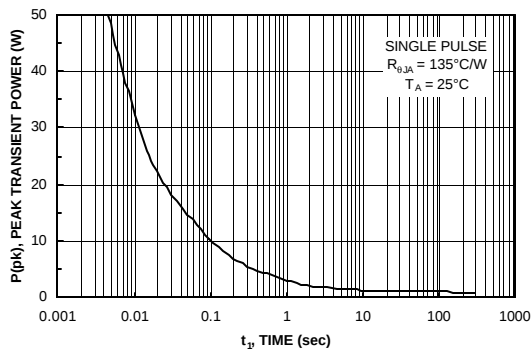


Figure 20. Single Pulse Maximum Power Dissipation.

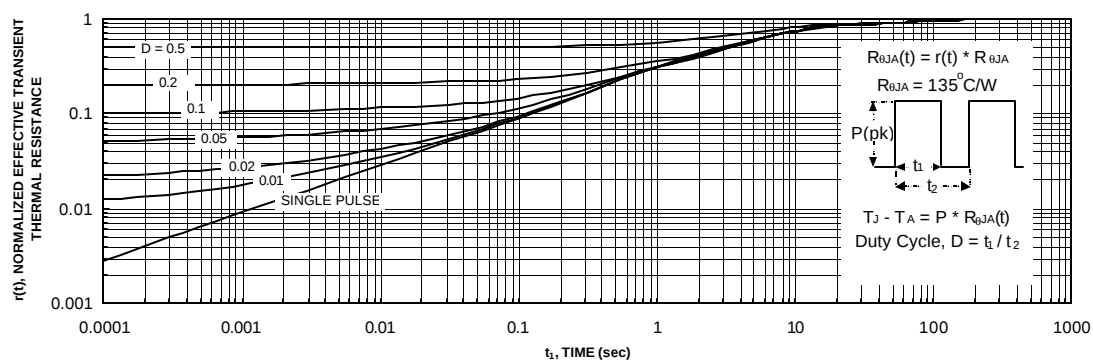


Figure 21. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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